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Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	36864
Number of I/O	133
Number of Gates	125000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	208-BFQFP
Supplier Device Package	208-PQFP (28x28)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3p125-2pq208

Power Consumption of Various Internal Resources

Table 2-14 • Different Components Contributing to Dynamic Power Consumption in ProASIC3 Devices

Parameter	Definition	Device Specific Dynamic Contributions ($\mu\text{W}/\text{MHz}$)							
		A3P1000	A3P600	A3P400	A3P250	A3P125	A3P060	A3P030	A3P015
PAC1	Clock contribution of a Global Rib	14.50	12.80	12.80	11.00	11.00	9.30	9.30	9.30
PAC2	Clock contribution of a Global Spine	2.48	1.85	1.35	1.58	0.81	0.81	0.41	0.41
PAC3	Clock contribution of a VersaTile row	0.81							
PAC4	Clock contribution of a VersaTile used as a sequential module	0.12							
PAC5	First contribution of a VersaTile used as a sequential module	0.07							
PAC6	Second contribution of a VersaTile used as a sequential module	0.29							
PAC7	Contribution of a VersaTile used as a combinatorial Module	0.29							
PAC8	Average contribution of a routing net	0.70							
PAC9	Contribution of an I/O input pin (standard dependent)	See Table 2-8 on page 2-7 through Table 2-10 on page 2-8 .							
PAC10	Contribution of an I/O output pin (standard dependent)	See Table 2-11 on page 2-9 through Table 2-13 on page 2-10 .							
PAC11	Average contribution of a RAM block during a read operation	25.00							
PAC12	Average contribution of a RAM block during a write operation	30.00							
PAC13	Dynamic contribution for PLL	2.60							

Note: *For a different output load, drive strength, or slew rate, Microsemi recommends using the Microsemi Power spreadsheet calculator or SmartPower tool in Libero SoC software.

Table 2-15 • Different Components Contributing to the Static Power Consumption in ProASIC3 Devices

Parameter	Definition	Device Specific Static Power (mW)							
		A3P1000	A3P600	A3P400	A3P250	A3P125	A3P060	A3P030	A3P015
PDC1	Array static power in Active mode	See Table 2-7 on page 2-7.							
PDC2	I/O input pin static power (standard-dependent)	See Table 2-8 on page 2-7 through Table 2-10 on page 2-8.							
PDC3	I/O output pin static power (standard-dependent)	See Table 2-11 on page 2-9 through Table 2-13 on page 2-10.							
PDC4	Static PLL contribution	2.55 mW							
PDC5	Bank quiescent power (VCCI-dependent)	See Table 2-7 on page 2-7.							

Note: *For a different output load, drive strength, or slew rate, Microsemi recommends using the Microsemi Power spreadsheet calculator or SmartPower tool in Libero SoC software.

Power Calculation Methodology

This section describes a simplified method to estimate power consumption of an application. For more accurate and detailed power estimations, use the SmartPower tool in Libero SoC software.

The power calculation methodology described below uses the following variables:

- The number of PLLs as well as the number and the frequency of each output clock generated
- The number of combinatorial and sequential cells used in the design
- The internal clock frequencies
- The number and the standard of I/O pins used in the design
- The number of RAM blocks used in the design
- Toggle rates of I/O pins as well as VersaTiles—guidelines are provided in Table 2-16 on page 2-14.
- Enable rates of output buffers—guidelines are provided for typical applications in Table 2-17 on page 2-14.
- Read rate and write rate to the memory—guidelines are provided for typical applications in Table 2-17 on page 2-14. The calculation should be repeated for each clock domain defined in the design.

Methodology

Total Power Consumption— P_{TOTAL}

$$P_{TOTAL} = P_{STAT} + P_{DYN}$$

P_{STAT} is the total static power consumption.

P_{DYN} is the total dynamic power consumption.

Total Static Power Consumption— P_{STAT}

$$P_{STAT} = P_{DC1} + N_{INPUTS} * P_{DC2} + N_{OUTPUTS} * P_{DC3}$$

N_{INPUTS} is the number of I/O input buffers used in the design.

$N_{OUTPUTS}$ is the number of I/O output buffers used in the design.

Total Dynamic Power Consumption— P_{DYN}

$$P_{DYN} = P_{CLOCK} + P_{S-CELL} + P_{C-CELL} + P_{NET} + P_{INPUTS} + P_{OUTPUTS} + P_{MEMORY} + P_{PLL}$$

Global Clock Contribution— P_{CLOCK}

$$P_{CLOCK} = (P_{AC1} + N_{SPINE} * P_{AC2} + N_{ROW} * P_{AC3} + N_{S-CELL} * P_{AC4}) * F_{CLK}$$

N_{SPINE} is the number of global spines used in the user design—guidelines are provided in the "Spine Architecture" section of the Global Resources chapter in the *ProASIC3 FPGA Fabric User's Guide*.

N_{ROW} is the number of VersaTile rows used in the design—guidelines are provided in the "Spine Architecture" section of the Global Resources chapter in the *ProASIC3 FPGA Fabric User's Guide*.

User I/O Characteristics

Timing Model

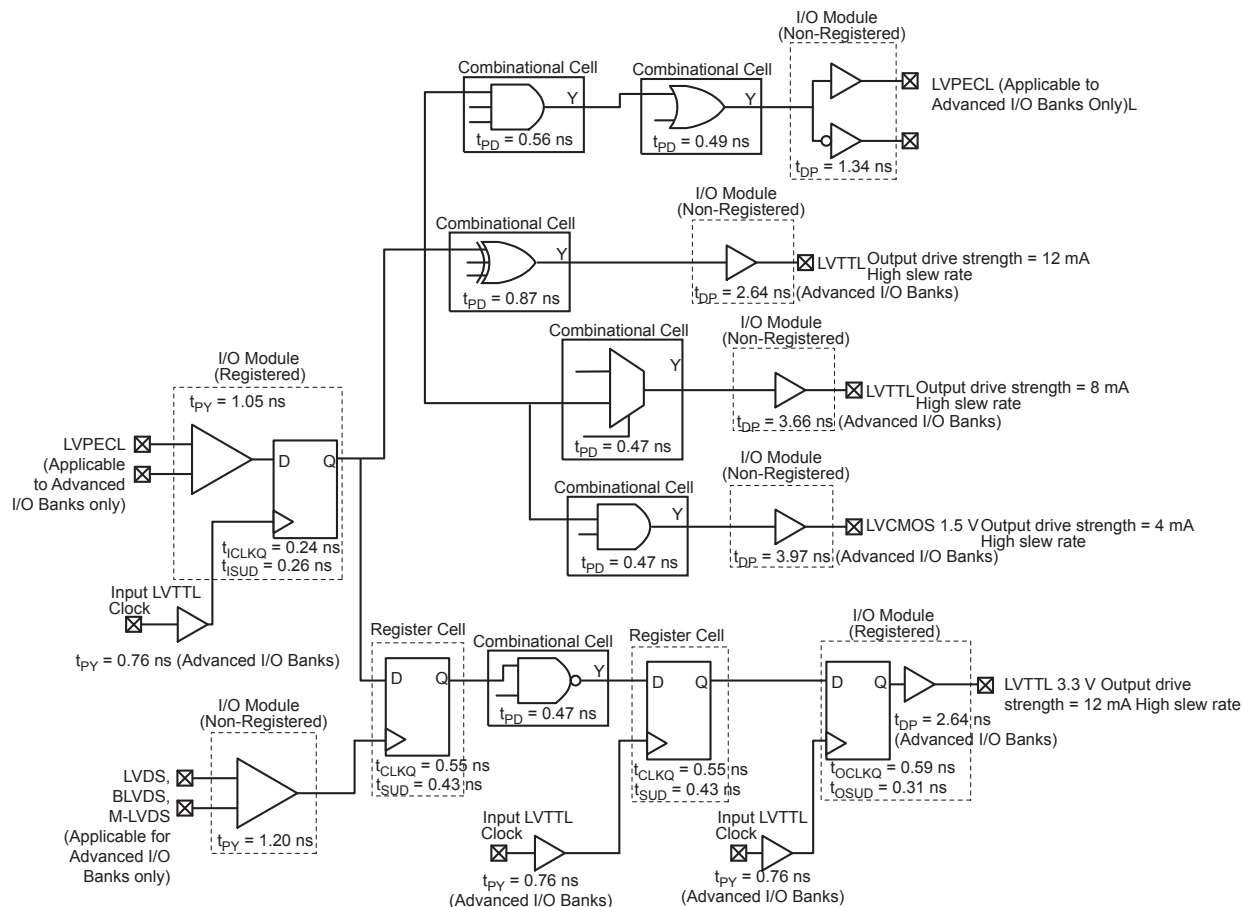


Figure 2-3 • Timing Model

Operating Conditions: –2 Speed, Commercial Temperature Range ($T_J = 70^\circ\text{C}$), Worst Case $V_{CC} = 1.425$ V

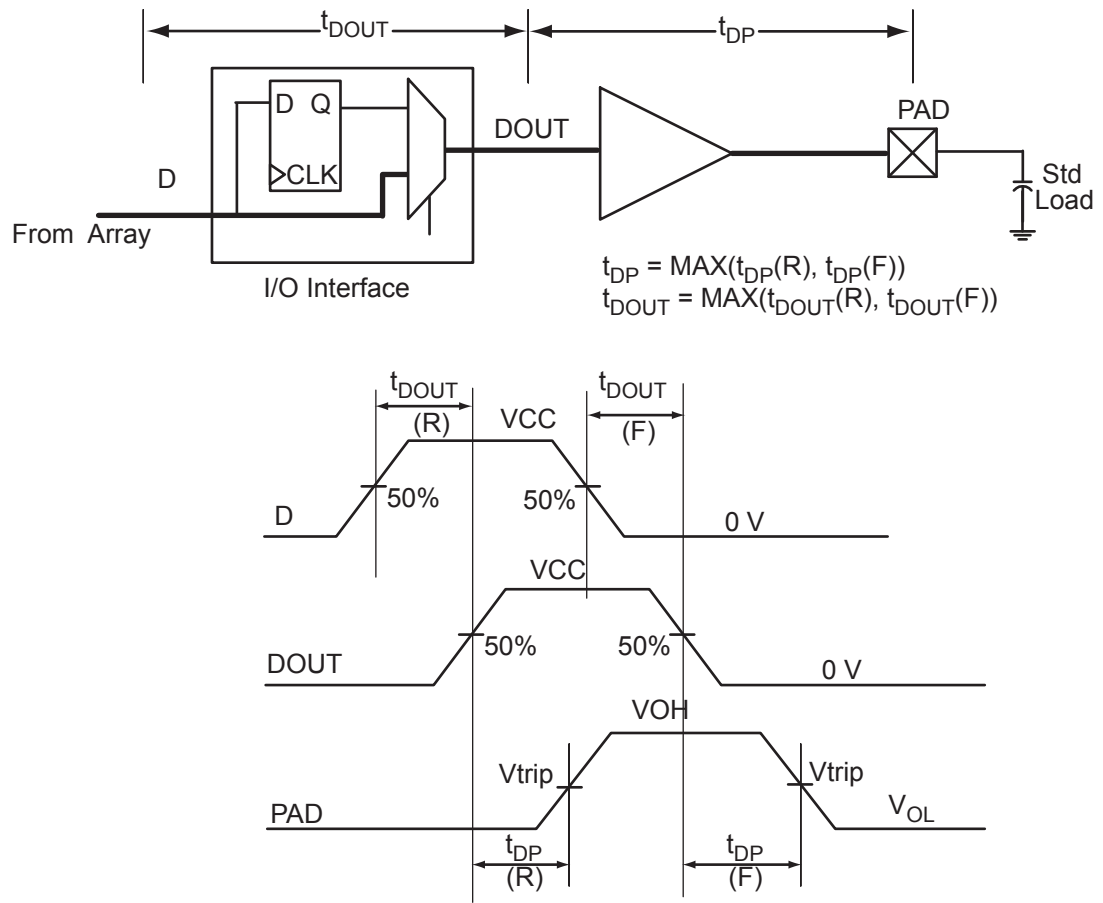


Figure 2-5 • Output Buffer Model and Delays (Example)

Overview of I/O Performance

Summary of I/O DC Input and Output Levels – Default I/O Software Settings

Table 2-18 • Summary of Maximum and Minimum DC Input and Output Levels Applicable to Commercial and Industrial Conditions—Software Default Settings
 Applicable to Advanced I/O Banks

I/O Standard	Drive Strength	Equiv. Software Default Drive Strength Option ²	Slew Rate	VIL		VIH		VOL	VOH	IOL ¹ mA	IOH ¹ mA
				Min V	Max V	Min V	Max V	Max V	Min V		
3.3 V LVTTTL / 3.3 V LVC MOS	12 mA	12 mA	High	−0.3	0.8	2	3.6	0.4	2.4	12	12
3.3 V LVC MOS Wide Range ³	100 μ A	12 mA	High	−0.3	0.8	2	3.6	0.2	VCCI − 0.2	0.1	0.1
2.5 V LVC MOS	12 mA	12 mA	High	−0.3	0.7	1.7	2.7	0.7	1.7	12	12
1.8 V LVC MOS	12 mA	12 mA	High	−0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI − 0.45	12	12
1.5 V LVC MOS	12 mA	12 mA	High	−0.3	0.35 * VCCI	0.65 * VCCI	1.6	0.25 * VCCI	0.75 * VCCI	12	12
3.3 V PCI	Per PCI specifications										
3.3 V PCI-X	Per PCI-X specifications										

Notes:

1. Currents are measured at 85°C junction temperature.
2. 3.3 V LVC MOS wide range is applicable to 100 μ A drive strength only. The configuration will NOT operate at the equivalent software default drive strength. These values are for Normal Ranges ONLY.
3. All LVC MOS 3.3 V software macros support LVC MOS 3.3 V wide range as specified in the JESD-8B specification.

Table 2-49 • Minimum and Maximum DC Input and Output Levels
Applicable to Standard I/O Banks

3.3 V LVCMOS Wide Range	Equiv. Software Default	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL ²	IIH ³
Drive Strength	Drive Strength Option ¹	Min V	Max V	Min V	Max V	Max V	Min V	μA	μA	Max mA ⁴	Max mA ⁴	μA ⁵	μA ⁵
100 μA	2 mA	−0.3	0.8	2	3.6	0.2	VDD − 0.2	100	100	25	27	10	10
100 μA	4 mA	−0.3	0.8	2	3.6	0.2	VDD − 0.2	100	100	25	27	10	10
100 μA	6 mA	−0.3	0.8	2	3.6	0.2	VDD − 0.2	100	100	51	54	10	10
100 μA	8 mA	−0.3	0.8	2	3.6	0.2	VDD − 0.2	100	100	51	54	10	10

Notes:

1. The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ±100 μA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
2. IIL is the input leakage current per I/O pin over recommended operation conditions where −0.3 V < VIN < VIL.
3. IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges
4. Currents are measured at 85°C junction temperature.
5. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD8-B specification.
6. Software default selection highlighted in gray.

Timing Characteristics

Table 2-50 • 3.3 V LVTTTL / 3.3 V LVCMOS High Slew

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 3.0\text{ V}$
 Applicable to Advanced I/O Banks

Drive Strength	Equiv. Software Default Drive Strength Option ¹	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
100 μA	4 mA	Std.	0.60	11.84	0.04	1.02	0.43	11.84	10.00	4.10	4.04	15.23	13.40	ns
		–1	0.51	10.07	0.04	0.86	0.36	10.07	8.51	3.48	3.44	12.96	11.40	ns
		–2	0.45	8.84	0.03	0.76	0.32	8.84	7.47	3.06	3.02	11.38	10.00	ns
100 μA	6 mA	Std.	0.60	7.59	0.04	1.02	0.43	7.59	6.18	4.62	4.95	10.98	9.57	ns
		–1	0.51	6.45	0.04	0.86	0.36	6.45	5.25	3.93	4.21	9.34	8.14	ns
		–2	0.45	5.67	0.03	0.76	0.32	5.67	4.61	3.45	3.70	8.20	7.15	ns
100 μA	8 mA	Std.	0.60	7.59	0.04	1.02	0.43	7.59	6.18	4.62	4.95	10.98	9.57	ns
		–1	0.51	6.45	0.04	0.86	0.36	6.45	5.25	3.93	4.21	9.34	8.14	ns
		–2	0.45	5.67	0.03	0.76	0.32	5.67	4.61	3.45	3.70	8.20	7.15	ns
100 μA	12 mA	Std.	0.60	5.46	0.04	1.02	0.43	5.46	4.29	4.97	5.54	8.86	7.68	ns
		–1	0.51	4.65	0.04	0.86	0.36	4.65	3.65	4.22	4.71	7.53	6.54	ns
		–2	0.45	4.08	0.03	0.76	0.32	4.08	3.20	3.71	4.14	6.61	5.74	ns
100 μA	16 mA	Std.	0.60	5.15	0.04	1.02	0.43	5.15	3.89	5.04	5.69	8.55	7.29	ns
		–1	0.51	4.38	0.04	0.86	0.36	4.38	3.31	4.29	4.84	7.27	6.20	ns
		–2	0.45	3.85	0.03	0.76	0.32	3.85	2.91	3.77	4.25	6.38	5.44	ns
100 μA	24 mA	Std.	0.60	4.75	0.04	1.02	0.43	4.75	3.22	5.14	6.28	8.15	6.61	ns
		–1	0.51	4.04	0.04	0.86	0.36	4.04	2.74	4.37	5.34	6.93	5.62	ns
		–2	0.45	3.55	0.03	0.76	0.32	3.55	2.40	3.84	4.69	6.09	4.94	ns

Notes:

1. The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is $\pm 100\text{ }\mu\text{A}$. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
2. Software default selection highlighted in gray.
3. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-81 • 1.5 V LVCMOS Low Slew

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 1.4\text{ V}$
 Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.66	12.78	0.04	1.44	0.43	12.81	12.78	3.40	2.64	15.05	15.02	ns
	–1	0.56	10.87	0.04	1.22	0.36	10.90	10.87	2.89	2.25	12.80	12.78	ns
	–2	0.49	9.55	0.03	1.07	0.32	9.57	9.55	2.54	1.97	11.24	11.22	ns
4 mA	Std.	0.66	10.01	0.04	1.44	0.43	10.19	9.55	3.75	3.27	12.43	11.78	ns
	–1	0.56	8.51	0.04	1.22	0.36	8.67	8.12	3.19	2.78	10.57	10.02	ns
	–2	0.49	7.47	0.03	1.07	0.32	7.61	7.13	2.80	2.44	9.28	8.80	ns
6 mA	Std.	0.66	9.33	0.04	1.44	0.43	9.51	8.89	3.83	3.43	11.74	11.13	ns
	–1	0.56	7.94	0.04	1.22	0.36	8.09	7.56	3.26	2.92	9.99	9.47	ns
	–2	0.49	6.97	0.03	1.07	0.32	7.10	6.64	2.86	2.56	8.77	8.31	ns
8 mA	Std.	0.66	8.91	0.04	1.44	0.43	9.07	8.89	3.95	4.05	11.31	11.13	ns
	–1	0.56	7.58	0.04	1.22	0.36	7.72	7.57	3.36	3.44	9.62	9.47	ns
	–2	0.49	6.65	0.03	1.07	0.32	6.78	6.64	2.95	3.02	8.45	8.31	ns
12 mA	Std.	0.66	8.91	0.04	1.44	0.43	9.07	8.89	3.95	4.05	11.31	11.13	ns
	–1	0.56	7.58	0.04	1.22	0.36	7.72	7.57	3.36	3.44	9.62	9.47	ns
	–2	0.49	6.65	0.03	1.07	0.32	6.78	6.64	2.95	3.02	8.45	8.31	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-82 • 1.5 V LVCMOS High Slew

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 1.4\text{ V}$
 Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.66	7.83	0.04	1.42	0.43	6.42	7.83	2.71	2.55	8.65	10.07	ns
	–1	0.56	6.66	0.04	1.21	0.36	5.46	6.66	2.31	2.17	7.36	8.56	ns
	–2	0.49	5.85	0.03	1.06	0.32	4.79	5.85	2.02	1.90	6.46	7.52	ns
4 mA	Std.	0.66	4.84	0.04	1.42	0.43	4.49	4.84	3.03	3.13	6.72	7.08	ns
	–1	0.56	4.12	0.04	1.21	0.36	3.82	4.12	2.58	2.66	5.72	6.02	ns
	–2	0.49	3.61	0.03	1.06	0.32	3.35	3.61	2.26	2.34	5.02	5.28	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-93 • Minimum and Maximum DC Input and Output Levels

DC Parameter	Description	Min.	Max.	Min.	Max.	Min.	Max.	Units
VCCI	Supply Voltage	3.0		3.3		3.6		V
VOL	Output Low Voltage	0.96	1.27	1.06	1.43	1.30	1.57	V
VOH	Output High Voltage	1.8	2.11	1.92	2.28	2.13	2.41	V
VIL, VIH	Input Low, Input High Voltages	0	3.6	0	3.6	0	3.6	V
VODIFF	Differential Output Voltage	0.625	0.97	0.625	0.97	0.625	0.97	V
VOCM	Output Common-Mode Voltage	1.762	1.98	1.762	1.98	1.762	1.98	V
VICM	Input Common-Mode Voltage	1.01	2.57	1.01	2.57	1.01	2.57	V
VIDIFF	Input Differential Voltage	300		300		300		mV

Table 2-94 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)
1.64	1.94	Cross point

Note: *Measuring point = V_{trip} . See [Table 2-22 on page 2-22](#) for a complete table of trip points.

Timing Characteristics

Table 2-95 • LVPECL

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V

Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	Units
Std.	0.66	1.80	0.04	1.40	ns
–1	0.56	1.53	0.04	1.19	ns
–2	0.49	1.34	0.03	1.05	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Output DDR Module

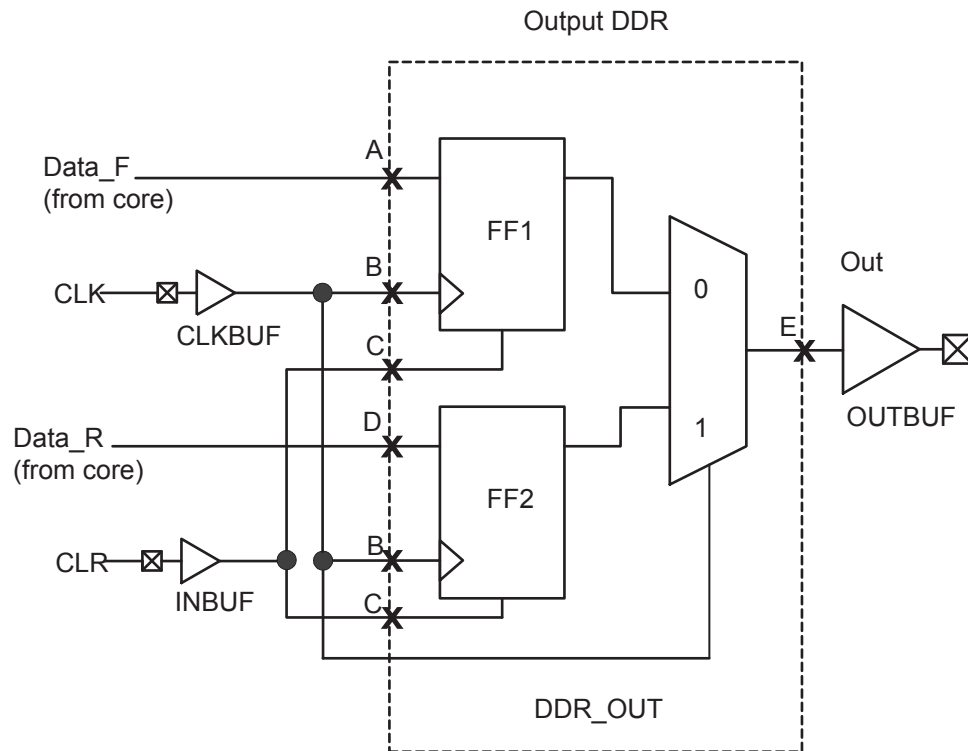


Figure 2-22 • Output DDR Timing Model

Table 2-103 • Parameter Definitions

Parameter Name	Parameter Definition	Measuring Nodes (from, to)
t_{DDROCLKQ}	Clock-to-Out	B, E
$t_{\text{DDROCLR2Q}}$	Asynchronous Clear-to-Out	C, E
$t_{\text{DDROREMCLR}}$	Clear Removal	C, B
$t_{\text{DDRORECCLR}}$	Clear Recovery	C, B
t_{DDROSUD1}	Data Setup Data_F	A, B
t_{DDROSUD2}	Data Setup Data_R	D, B
t_{DDROHD1}	Data Hold Data_F	A, B
t_{DDROHD2}	Data Hold Data_R	D, B

Table 2-109 • A3P060 Global Resource
Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, $V_{CC} = 1.425\text{ V}$

Parameter	Description	-2		-1		Std.		Units
		Min. ¹	Max. ²	Min. ¹	Max. ²	Min. ¹	Max. ²	
t_{RCKL}	Input Low Delay for Global Clock	0.71	0.93	0.81	1.05	0.95	1.24	ns
t_{RCKH}	Input High Delay for Global Clock	0.70	0.96	0.80	1.09	0.94	1.28	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	0.75		0.85		1.00		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	0.85		0.96		1.13		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.26		0.29		0.34	ns

Notes:

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).
2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).
3. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-110 • A3P125 Global Resource
Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, $V_{CC} = 1.425\text{ V}$

Parameter	Description	-2		-1		Std.		Units
		Min. ¹	Max. ²	Min. ¹	Max. ²	Min. ¹	Max. ²	
t_{RCKL}	Input Low Delay for Global Clock	0.77	0.99	0.87	1.12	1.03	1.32	ns
t_{RCKH}	Input High Delay for Global Clock	0.76	1.02	0.87	1.16	1.02	1.37	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	0.75		0.85		1.00		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	0.85		0.96		1.13		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.26		0.29		0.34	ns

Notes:

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).
2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).
3. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-117 • RAM512X18**Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$**

Parameter	Description	-2	-1	Std.	Units
t_{AS}	Address setup time	0.25	0.28	0.33	ns
t_{AH}	Address hold time	0.00	0.00	0.00	ns
t_{ENS}	REN, WEN setup time	0.13	0.15	0.17	ns
t_{ENH}	REN, WEN hold time	0.10	0.11	0.13	ns
t_{DS}	Input data (WD) setup time	0.18	0.21	0.25	ns
t_{DH}	Input data (WD) hold time	0.00	0.00	0.00	ns
t_{CKQ1}	Clock High to new data valid on RD (output retained)	2.16	2.46	2.89	ns
t_{CKQ2}	Clock High to new data valid on RD (pipelined)	0.90	1.02	1.20	ns
t_{C2CRWH}^1	Address collision clk-to-clk delay for reliable read access after write on same address—Applicable to Opening Edge	0.50	0.43	0.38	ns
t_{C2CWRH}^1	Address collision clk-to-clk delay for reliable write access after read on same address—Applicable to Opening Edge	0.59	0.50	0.44	ns
t_{RSTBQ}	RESET Low to data out Low on RD (flow-through)	0.92	1.05	1.23	ns
	RESET Low to data out Low on RD (pipelined)	0.92	1.05	1.23	ns
$t_{REMRSTB}$	RESET removal	0.29	0.33	0.38	ns
$t_{RECRSTB}$	RESET recovery	1.50	1.71	2.01	ns
$t_{MPWRSTB}$	RESET minimum pulse width	0.21	0.24	0.29	ns
t_{CYC}	Clock cycle time	3.23	3.68	4.32	ns
F_{MAX}	Maximum frequency	310	272	231	MHz

Notes:

1. For more information, refer to the application note [Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs](#).
2. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

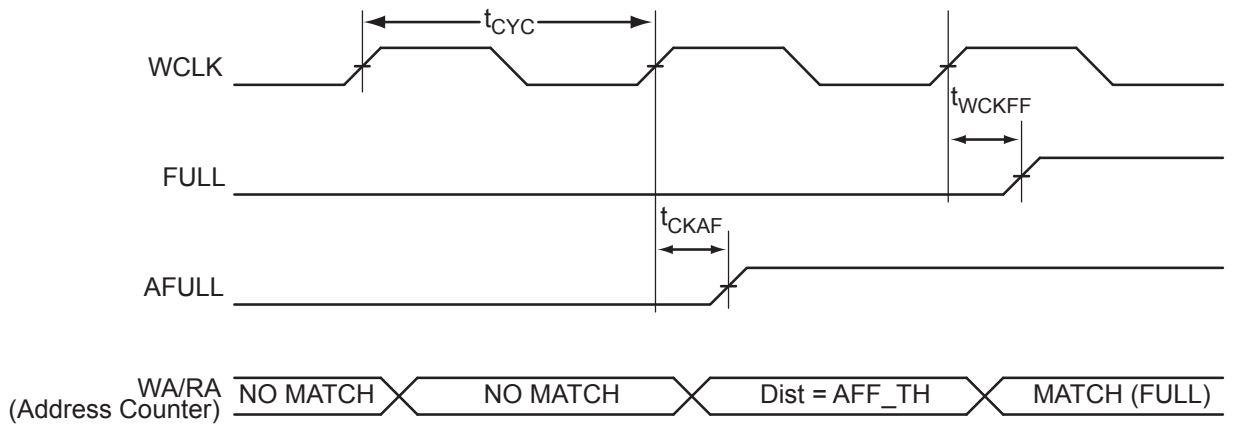


Figure 2-41 • FIFO FULL Flag and AFULL Flag Assertion

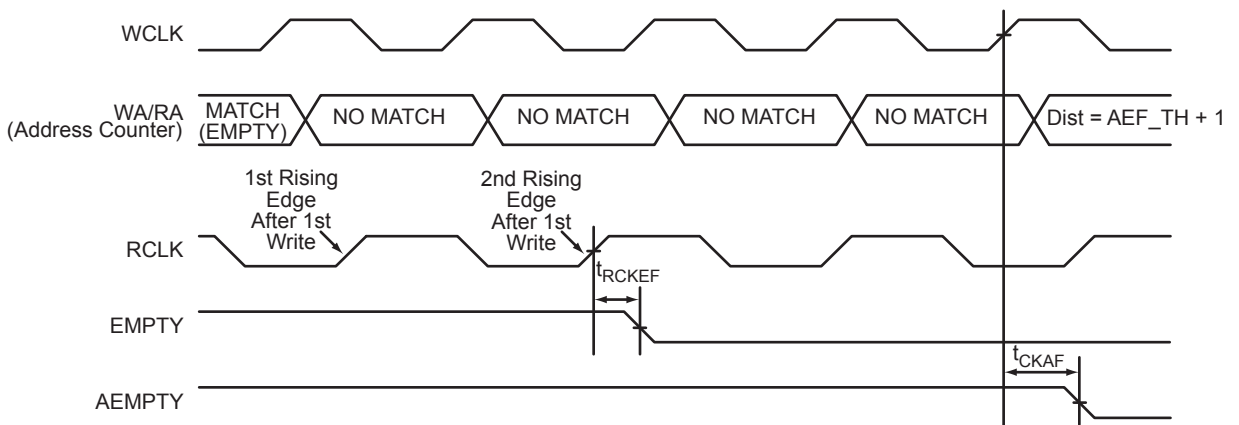


Figure 2-42 • FIFO EMPTY Flag and AEMPTY Flag Deassertion

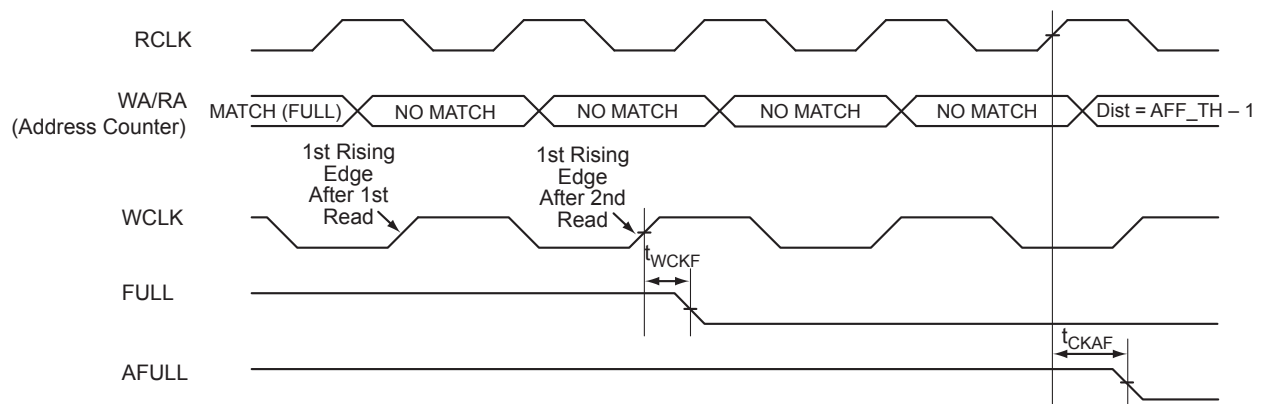


Figure 2-43 • FIFO FULL Flag and AFULL Flag Deassertion

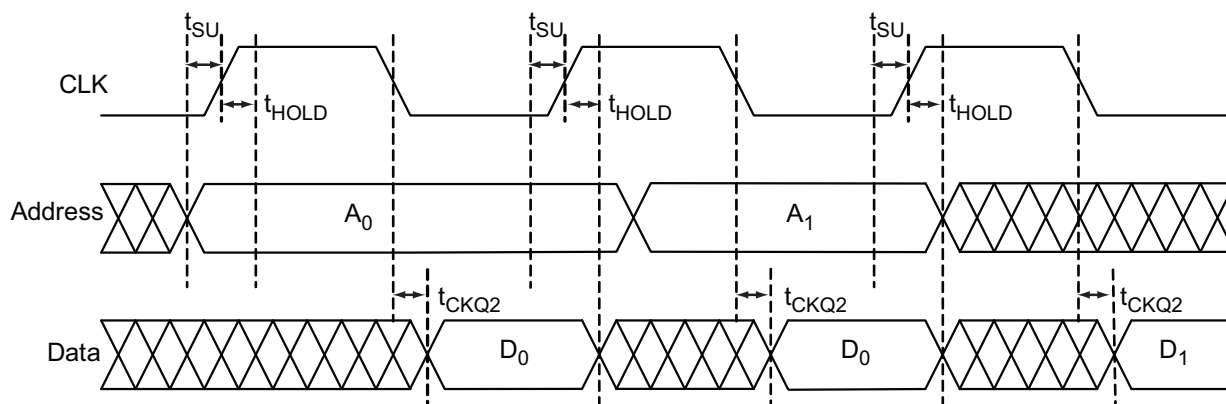
Table 2-120 • A3P250 FIFO 512×8
Worst Commercial-Case Conditions: $T_J = 70^{\circ}\text{C}$, $V_{CC} = 1.425\text{ V}$

Parameter	Description	–2	–1	Std.	Units
t_{ENS}	REN, WEN Setup Time	3.75	4.27	5.02	ns
t_{ENH}	REN, WEN Hold Time	0.00	0.00	0.00	ns
t_{BKS}	BLK Setup Time	0.19	0.22	0.26	ns
t_{BKH}	BLK Hold Time	0.00	0.00	0.00	ns
t_{DS}	Input Data (WD) Setup Time	0.18	0.21	0.25	ns
t_{DH}	Input Data (WD) Hold Time	0.00	0.00	0.00	ns
t_{CKQ1}	Clock High to New Data Valid on RD (flow-through)	2.17	2.47	2.90	ns
t_{CKQ2}	Clock High to New Data Valid on RD (pipelined)	0.94	1.07	1.26	ns
t_{RCKEF}	RCLK High to Empty Flag Valid	1.72	1.96	2.30	ns
t_{WCKFF}	WCLK High to Full Flag Valid	1.63	1.86	2.18	ns
t_{CKAF}	Clock High to Almost Empty/Full Flag Valid	6.19	7.05	8.29	ns
t_{RSTFG}	RESET Low to Empty/Full Flag Valid	1.69	1.93	2.27	ns
t_{RSTAF}	RESET Low to Almost Empty/Full Flag Valid	6.13	6.98	8.20	ns
t_{RSTBQ}	RESET Low to Data Out Low on RD (flow-through)	0.92	1.05	1.23	ns
	RESET Low to Data Out Low on RD (pipelined)	0.92	1.05	1.23	ns
t_{REMRSTB}	RESET Removal	0.29	0.33	0.38	ns
t_{RECRSTB}	RESET Recovery	1.50	1.71	2.01	ns
t_{MPWRSTB}	RESET Minimum Pulse Width	0.21	0.24	0.29	ns
t_{CYC}	Clock Cycle Time	3.23	3.68	4.32	ns
F_{MAX}	Maximum Frequency for FIFO	310	272	231	MHz

Table 2-123 • A3P250 FIFO 4k×1 (continued)**Worst Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, $V_{CC} = 1.425\text{ V}$**

Parameter	Description	-2	-1	Std.	Units
t_{RSTAF}	RESET Low to Almost Empty/Full Flag Valid	6.13	6.98	8.20	ns
t_{RSTBQ}	RESET Low to Data Out Low on DO (pass-through)	0.92	1.05	1.23	ns
	RESET Low to Data Out Low on DO (pipelined)	0.92	1.05	1.23	ns
t_{REMRSTB}	RESET Removal	0.29	0.33	0.38	ns
t_{RECRSTB}	RESET Recovery	1.50	1.71	2.01	ns
t_{MPWRSTB}	RESET Minimum Pulse Width	0.21	0.24	0.29	ns
t_{CYC}	Clock Cycle Time	3.23	3.68	4.32	ns
F_{MAX}	Maximum Frequency	310	272	231	MHz

Embedded FlashROM Characteristics

**Figure 2-44 • Timing Diagram**

Timing Characteristics

Table 2-124 • Embedded FlashROM Access Time

Parameter	Description	-2	-1	Std.	Units
t_{SU}	Address Setup Time	0.53	0.61	0.71	ns
t_{HOLD}	Address Hold Time	0.00	0.00	0.00	ns
t_{CK2Q}	Clock to Out	21.42	24.40	28.68	ns
F_{MAX}	Maximum Clock Frequency	15	15	15	MHz

PQ208	
Pin Number	A3P1000 Function
109	TRST
110	VJTAG
111	GDA0/IO113NDB1
112	GDA1/IO113PDB1
113	GDB0/IO112NDB1
114	GDB1/IO112PDB1
115	GDC0/IO111NDB1
116	GDC1/IO111PDB1
117	IO109NDB1
118	IO109PDB1
119	IO106NDB1
120	IO106PDB1
121	IO104PSB1
122	GND
123	VCCIB1
124	IO99NDB1
125	IO99PDB1
126	NC
127	IO96NDB1
128	GCC2/IO96PDB1
129	GCB2/IO95PSB1
130	GND
131	GCA2/IO94PSB1
132	GCA1/IO93PDB1
133	GCA0/IO93NDB1
134	GCB0/IO92NDB1
135	GCB1/IO92PDB1
136	GCC0/IO91NDB1
137	GCC1/IO91PDB1
138	IO88NDB1
139	IO88PDB1
140	VCCIB1
141	GND
142	VCC
143	IO86PSB1
144	IO84NDB1

PQ208	
Pin Number	A3P1000 Function
145	IO84PDB1
146	IO82NDB1
147	IO82PDB1
148	IO80NDB1
149	GBC2/IO80PDB1
150	IO79NDB1
151	GBB2/IO79PDB1
152	IO78NDB1
153	GBA2/IO78PDB1
154	VMV1
155	GNDQ
156	GND
157	VMV0
158	GBA1/IO77RSB0
159	GBA0/IO76RSB0
160	GBB1/IO75RSB0
161	GBB0/IO74RSB0
162	GND
163	GBC1/IO73RSB0
164	GBC0/IO72RSB0
165	IO70RSB0
166	IO67RSB0
167	IO63RSB0
168	IO60RSB0
169	IO57RSB0
170	VCCIB0
171	VCC
172	IO54RSB0
173	IO51RSB0
174	IO48RSB0
175	IO45RSB0
176	IO42RSB0
177	IO40RSB0
178	GND
179	IO38RSB0
180	IO35RSB0

PQ208	
Pin Number	A3P1000 Function
181	IO33RSB0
182	IO31RSB0
183	IO29RSB0
184	IO27RSB0
185	IO25RSB0
186	VCCIB0
187	VCC
188	IO22RSB0
189	IO20RSB0
190	IO18RSB0
191	IO16RSB0
192	IO15RSB0
193	IO14RSB0
194	IO13RSB0
195	GND
196	IO12RSB0
197	IO11RSB0
198	IO10RSB0
199	IO09RSB0
200	VCCIB0
201	GAC1/IO05RSB0
202	GAC0/IO04RSB0
203	GAB1/IO03RSB0
204	GAB0/IO02RSB0
205	GAA1/IO01RSB0
206	GAA0/IO00RSB0
207	GNDQ
208	VMV0

FG144	
Pin Number	A3P600 Function
A1	GNDQ
A2	VMV0
A3	GAB0/IO02RSB0
A4	GAB1/IO03RSB0
A5	IO10RSB0
A6	GND
A7	IO34RSB0
A8	VCC
A9	IO50RSB0
A10	GBA0/IO58RSB0
A11	GBA1/IO59RSB0
A12	GNDQ
B1	GAB2/IO173PDB3
B2	GND
B3	GAA0/IO00RSB0
B4	GAA1/IO01RSB0
B5	IO13RSB0
B6	IO19RSB0
B7	IO31RSB0
B8	IO39RSB0
B9	GBB0/IO56RSB0
B10	GBB1/IO57RSB0
B11	GND
B12	VMV1
C1	IO173NDB3
C2	GFA2/IO161PPB3
C3	GAC2/IO172PDB3
C4	VCC
C5	IO16RSB0
C6	IO25RSB0
C7	IO28RSB0
C8	IO42RSB0
C9	IO45RSB0
C10	GBA2/IO60PDB1
C11	IO60NDB1
C12	GBC2/IO62PPB1

FG144	
Pin Number	A3P600 Function
D1	IO169PDB3
D2	IO169NDB3
D3	IO172NDB3
D4	GAA2/IO174PPB3
D5	GAC0/IO04RSB0
D6	GAC1/IO05RSB0
D7	GBC0/IO54RSB0
D8	GBC1/IO55RSB0
D9	GBB2/IO61PDB1
D10	IO61NDB1
D11	IO62NPB1
D12	GCB1/IO70PPB1
E1	VCC
E2	GFC0/IO164NDB3
E3	GFC1/IO164PDB3
E4	VCCIB3
E5	IO174NPB3
E6	VCCIB0
E7	VCCIB0
E8	GCC1/IO69PDB1
E9	VCCIB1
E10	VCC
E11	GCA0/IO71NDB1
E12	IO72NDB1
F1	GFB0/IO163NPB3
F2	VCOMPLF
F3	GFB1/IO163PPB3
F4	IO161NPB3
F5	GND
F6	GND
F7	GND
F8	GCC0/IO69NDB1
F9	GCB0/IO70NPB1
F10	GND
F11	GCA1/IO71PDB1
F12	GCA2/IO72PDB1

FG144	
Pin Number	A3P600 Function
G1	GFA1/IO162PPB3
G2	GND
G3	VCCPLF
G4	GFA0/IO162NPB3
G5	GND
G6	GND
G7	GND
G8	GDC1/IO86PPB1
G9	IO74NDB1
G10	GCC2/IO74PDB1
G11	IO73NDB1
G12	GCB2/IO73PDB1
H1	VCC
H2	GFB2/IO160PDB3
H3	GFC2/IO159PSB3
H4	GEC1/IO146PDB3
H5	VCC
H6	IO80PDB1
H7	IO80NDB1
H8	GDB2/IO90RSB2
H9	GDC0/IO86NPB1
H10	VCCIB1
H11	IO84PSB1
H12	VCC
J1	GEB1/IO145PDB3
J2	IO160NDB3
J3	VCCIB3
J4	GEC0/IO146NDB3
J5	IO129RSB2
J6	IO131RSB2
J7	VCC
J8	TCK
J9	GDA2/IO89RSB2
J10	TDO
J11	GDA1/IO88PDB1
J12	GDB1/IO87PDB1

FG256	
Pin Number	A3P1000 Function
R5	IO168RSB2
R6	IO163RSB2
R7	IO157RSB2
R8	IO149RSB2
R9	IO143RSB2
R10	IO138RSB2
R11	IO131RSB2
R12	IO125RSB2
R13	GDB2/IO115RSB2
R14	TDI
R15	GNDQ
R16	TDO
T1	GND
T2	IO183RSB2
T3	GEB2/IO186RSB2
T4	IO172RSB2
T5	IO170RSB2
T6	IO164RSB2
T7	IO158RSB2
T8	IO153RSB2
T9	IO142RSB2
T10	IO135RSB2
T11	IO130RSB2
T12	GDC2/IO116RSB2
T13	IO120RSB2
T14	GDA2/IO114RSB2
T15	TMS
T16	GND

Revision	Changes	Page
Revision 5 (Aug 2008) DC and Switching Characteristics v1.3	T _J , Maximum Junction Temperature, was changed to 100° from 110° in the "Thermal Characteristics" section and EQ 1. The calculated result of Maximum Power Allowed has thus changed to 1.463 W from 1.951 W.	2-6
	Values for the A3P015 device were added to Table 2-7 • Quiescent Supply Current Characteristics.	2-7
	Values for the A3P015 device were added to Table 2-14 • Different Components Contributing to Dynamic Power Consumption in ProASIC3 Devices. P _{AC14} was removed. Table 2-15 • Different Components Contributing to the Static Power Consumption in ProASIC3 Devices is new.	2-11, 2-12
	The "PLL Contribution—P _{PLL} " section was updated to change the P _{PLL} formula from P _{AC13} + P _{AC14} * F _{CLKOUT} to P _{DC4} + P _{AC13} * F _{CLKOUT} .	2-14
	Both fall and rise values were included for t _{DDRISUD} and t _{DDRIHD} in Table 2-102 • Input DDR Propagation Delays.	2-78
	Table 2-107 • A3P015 Global Resource is new.	2-86
	The typical value for Delay Increments in Programmable Delay Blocks was changed from 160 to 200 in Table 2-115 • ProASIC3 CCC/PLL Specification.	2-90
Revision 4 (Jun 2008) DC and Switching Characteristics v1.2	Table note references were added to Table 2-2 • Recommended Operating Conditions 1, and the order of the table notes was changed.	2-2
	The title for Table 2-4 • Overshoot and Undershoot Limits 1 was modified to remove "as measured on quiet I/Os." Table note 1 was revised to remove "estimated SSO density over cycles." Table note 2 was revised to remove "refers only to overshoot/undershoot limits for simultaneous switching I/Os."	2-3
	The "Power per I/O Pin" section was updated to include 3 additional tables pertaining to input buffer power and output buffer power.	2-7
	Table 2-29 • I/O Output Buffer Maximum Resistances 1 was revised to include values for 3.3 V PCI/PCI-X.	2-27
	Table 2-90 • LVDS Minimum and Maximum DC Input and Output Levels was updated.	2-66
Revision 3 (Jun 2008) Packaging v1.3	Pin numbers were added to the "QN68 – Bottom View" package diagram. Note 2 was added below the diagram.	4-3
	The "QN132 – Bottom View" package diagram was updated to include D1 to D4. In addition, note 1 was changed from top view to bottom view, and note 2 is new.	4-6
Revision 2 (Feb 2008) Product Brief v1.0	This document was divided into two sections and given a version number, starting at v1.0. The first section of the document includes features, benefits, ordering information, and temperature and speed grade offerings. The second section is a device family overview.	N/A
	This document was updated to include A3P015 device information. QN68 is a new package that was added because it is offered in the A3P015. The following sections were updated: "Features and Benefits" "ProASIC3 Ordering Information" "Temperature Grade Offerings" "ProASIC3 Flash Family FPGAs" "A3P015 and A3P030" note Introduction and Overview (NA)	N/A

Revision	Changes	Page
Revision 2 (cont'd)	The "ProASIC3 FPGAs Package Sizes Dimensions" table is new.	III
	In the "ProASIC3 Ordering Information", the QN package measurements were updated to include both 0.4 mm and 0.5 mm.	IV
	In the General Description section the number of I/Os was updated from 288 to 300.	1-1
	The "QN68 – Bottom View" section is new.	4-3
Packaging v1.2		
Revision 1 (Feb 2008) DC and Switching Characteristics v1.1	In Table 2-2 • Recommended Operating Conditions 1, T_J was listed in the symbol column and was incorrect. It was corrected and changed to T_A .	2-2
	In Table 2-3 • Flash Programming Limits – Retention, Storage and Operating Temperature, Maximum Operating Junction Temperature was changed from 110°C to 100°C for both commercial and industrial grades.	2-3
	The "PLL Behavior at Brownout Condition" section is new.	2-4
	In the "PLL Contribution—PPLL" section, the following was deleted: FCLKIN is the input clock frequency.	2-14
	In Table 2-21 • Summary of Maximum and Minimum DC Input Levels, the note was incorrect. It previously said T_J and it was corrected and changed to T_A .	2-21
	In Table 2-115 • ProASIC3 CCC/PLL Specification, the SCLK parameter and note 1 are new.	2-90
	Table 2-125 • JTAG 1532 was populated with the parameter data, which was not in the previous version of the document.	2-108
	In the "VQ100" A3P030 pin table, the function of pin 63 was incorrect and changed from IO39RSB0 to GDB0/IO38RSB0.	4-19
Packaging v1.1		
Revision 0 (Jan 2008)	This document was previously in datasheet v2.2. As a result of moving to the handbook format, Actel has restarted the version numbers.	N/A
v2.2 (July 2007)	The M7 and M1 device part numbers have been updated in Table 1 • ProASIC3 Product Family, "I/Os Per Package", "Automotive ProASIC3 Ordering Information", "Temperature Grade Offerings", and "Speed Grade and Temperature Grade Matrix".	i, ii, iii, iii, iv
	The words "ambient temperature" were added to the temperature range in the "Automotive ProASIC3 Ordering Information", "Temperature Grade Offerings", and "Speed Grade and Temperature Grade Matrix" sections.	iii, iv
	The T_J parameter in Table 3-2 • Recommended Operating Conditions was changed to T_A , ambient temperature, and table notes 4–6 were added.	3-2
v2.1 (May 2007)	In the "Clock Conditioning Circuit (CCC) and PLL" section, the Wide Input Frequency Range (1.5 MHz to 200 MHz) was changed to (1.5 MHz to 350 MHz).	i
	The "Clock Conditioning Circuit (CCC) and PLL" section was updated.	i
	In the "I/Os Per Package" section, the A3P030, A3P060, A3P125, ACP250, and A3P600 device I/Os were updated.	ii
	Table 3-5 • Package Thermal Resistivities was updated with A3P1000 information. The note below the table is also new.	3-5